



Microprocessor Supervisory Circuit

ADM1232A

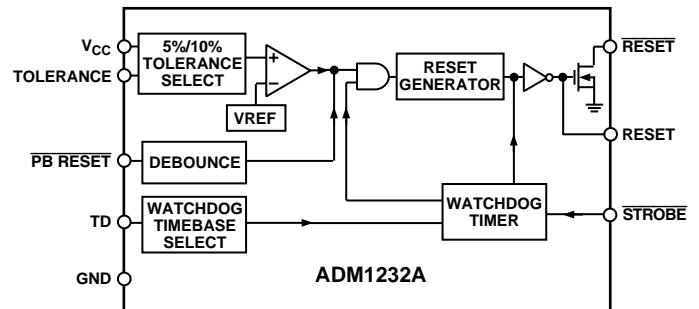
FEATURES

- Superior Upgrade for MAX1232 and Dallas DS1232
- Low Power Consumption (500 μ A max)
- Adjustable Precision Voltage Monitor with +4.5 V and +4.75 V Options
- Adjustable STROBE Monitor with 150 ms, 600 ms or 1.2 sec Options
- No External Components
- Fast (20 ns) Strobe Pulsewidth

APPLICATIONS

- Microprocessor Systems
- Portable Equipment
- Computers
- Controllers
- Intelligent Instruments
- Automotive Systems
- Protection Against Damage Caused by μ P Failure

FUNCTIONAL BLOCK DIAGRAM



GENERAL DESCRIPTION

The ADM1232A is a superior, pin-compatible upgrade for the MAX1232 and the DS1232LP and DS1232. The ADM1232A can detect strobe pulsewidths as narrow as 20 ns, making it compatible with high speed microprocessors. The Analog Devices ADM1232A is a microprocessor monitoring circuit that can monitor:

1. Microprocessor Supply Voltage.
2. Whether a Microprocessor has locked up.
3. An External Interrupt.

The ADM1232A is available in four different packages:

1. The ADM1232AARM in an 8-lead μ SOIC (RM-8).
2. The ADM1232AAN in an 8-lead PDIP (N-8).
3. The ADM1232AARW in a 16-lead wide SOIC (R-16).
4. The ADM1232AARN is an 8-lead narrow SOIC (R-8).

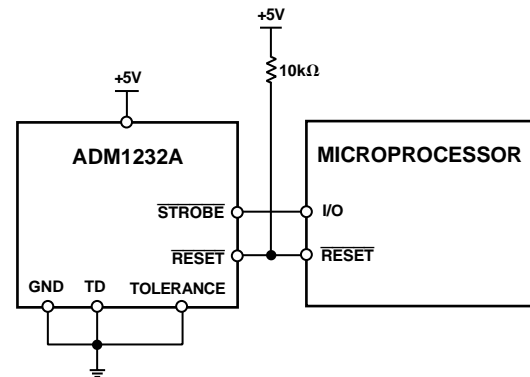


Figure 1. Typical Supply Monitoring Application

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ADM1232A—SPECIFICATIONS (V_{CC} = Full Operating Range, T_A = T_{MIN} to T_{MAX} unless otherwise noted)

| Parameter | Min | Typ | Max | Units | Test Conditions/Comments |
|--|-----------------------|-----------------------|-----------------------|-------|--|
| TEMPERATURE | -40 | | +85 | °C | T _A = T _{MIN} to T _{MAX} |
| POWER SUPPLY | | | | | |
| Voltage | 4.5 | 5.0 | 5.5 | V | V _{IL} , V _{IH} = CMOS Levels V _{IL} , V _{IH} = TTL Levels |
| Current | | 20 | 50 | μA | |
| | | 200 | 500 | μA | |
| STROBE AND PB RESET INPUTS | | | | | |
| Input High Level | 2.0 | | V _{CC} + 0.3 | V | |
| Input Low Level | -0.3 | | +0.8 | V | |
| INPUT LEAKAGE CURRENT (STROBE, TOLERANCE) | | | | | |
| TD | -1.0 | 1.6 | +1.0 | μA | |
| OUTPUT CURRENT | | | | | |
| RESET | 8 | 10 | | mA | When V _{CC} Is at 4.5 V–5.5 V When V _{CC} Is at 4.5 V–5.5 V |
| RESET, RESET | -8 | -12 | | mA | |
| OUTPUT VOLTAGE | | | | | |
| RESET/RESET | V _{CC} - 0.5 | V _{CC} - 0.1 | | V | While sourcing less than 500 μA, RESET remains within 0.5 V of V _{CC} on power-down until V _{CC} drops below 2.0 V. While sinking less than 500 μA, RESET remains within 0.5 V of GND on power-down until V _{CC} drops below 2.0 V. |
| RESET/RESET High Level | | | 0.4 | V | |
| RESET/RESET Low Level | 2.4 | | | V | |
| 1 V OPERATION | | | | | |
| RESET Output Voltage | | V _{CC} - 0.1 | | V | While Sourcing Less than 50 μA While Sinking Less than 50 μA |
| RESET Output Voltage | | 0.1 | | V | |
| V _{CC} TRIP POINT | | | | | |
| 5% | 4.5 | 4.62 | 4.74 | V | TOLERANCE = GND |
| 10% | 4.25 | 4.37 | 4.49 | V | TOLERANCE = V _{CC} |
| CAPACITANCE | | | | | |
| Input (STROBE, TOLERANCE) | | | 5 | pF | T _A = +25°C T _A = +25°C |
| Output (RESET, RESET) | | | 7 | pF | |
| PB RESET | | | | | |
| Time | 20 | | | ms | PB RESET Must Be Held Low for a Minimum of 20 ms to Guarantee a Reset |
| Delay | 1 | 4 | 20 | ms | |
| RESET ACTIVE TIME | 250 | 610 | 1000 | ms | |
| STROBE | | | | | |
| Pulsewidth | 20 | | | ns | TD = 0 V TD = Floating TD = V _{CC} |
| Timeout Period | 62.5 | 150 | 250 | ms | |
| | 250 | 600 | 1000 | ms | |
| | 500 | 1200 | 2000 | ms | |
| V _{CC} | | | | | |
| Fall Time | 10 | | | μs | Guaranteed by Design |
| Rise Time | 0 | | | μs | Guaranteed by Design |
| V _{CC} FAIL DETECT TO RESET OUTPUT DELAY RESET AND RESET Are Logically Correct | | | | | |
| | | | 50 | μs | After V _{CC} Falls Below the Set Tolerance Voltage (Figure 5) |
| | 250 | 610 | 1000 | ms | After V _{CC} Rises Above the Set Tolerance Voltage |

Specifications subject to change without notice.

ABSOLUTE MAXIMUM RATINGS*

(T_A = +25°C unless otherwise noted)

| | |
|--|-----------------------------------|
| V _{CC} | +5.5 V |
| Logic Inputs | -0.3 V to V _{CC} + 0.3 V |
| Storage Temperature Range | -65°C to +150°C |
| Lead Temperature (Soldering, 10 sec) | +300°C |
| Vapor Phase (60 sec) | +215°C |
| Infrared (15 sec) | +220°C |

N-8

| | |
|---|---------|
| Power Dissipation | 1000 mW |
| Derate by 13.5 mW/°C above 25°C | |
| θ _{JA} Thermal Impedance | 100°C/W |

R-16

| | |
|---|--------|
| Power Dissipation | 900 mW |
| Derate by 12 mW/°C above 25°C | |
| θ _{JA} Thermal Impedance (Still Air) | 73°C/W |

RM-8

| | |
|---|---------|
| Power Dissipation | 900 mW |
| Derate by 12 mW/°C above 25°C | |
| θ _{JA} Thermal Impedance (Still Air) | 206°C/W |

R-8

| | |
|---|---------|
| Power Dissipation | 900 μW |
| Derate by 12 mW/°C above 25°C | |
| θ _{JA} Thermal Impedance (Still Air) | 153°C/W |

*Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum ratings for extended periods of time may affect device reliability.

ORDERING GUIDE

| Model | Temperature Range | Package Options* |
|-------------|-------------------|------------------|
| ADM1232AARM | -40°C to +85°C | RM-8 |
| ADM1232AAN | -40°C to +85°C | N-8 |
| ADM1232AARW | -40°C to +85°C | R-16 |
| ADM1232AARN | -40°C to +85°C | R-8 |

*N = Plastic DIP; R = Small Outline; RM = μSOIC.

CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADM1232A features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.

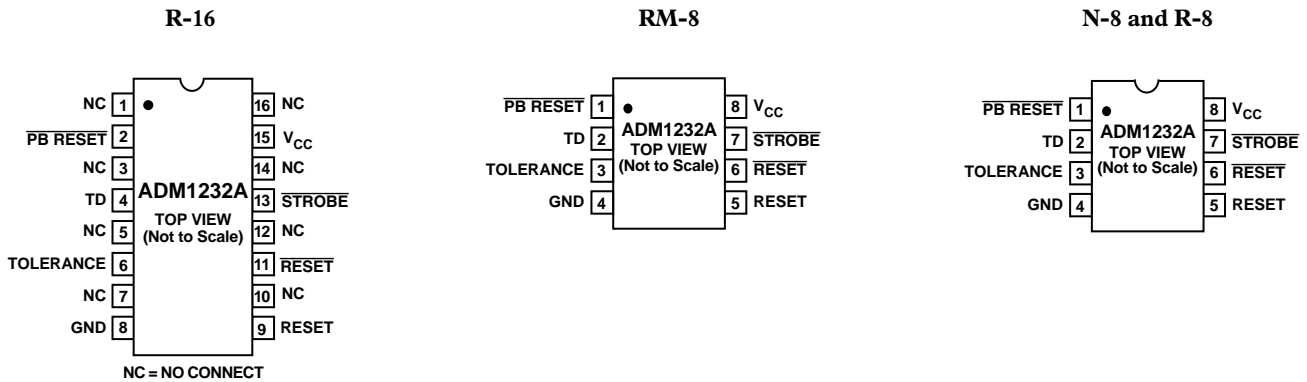


ADM1232A

PIN FUNCTION DESCRIPTIONS

| Mnemonic | Function |
|------------------------------|--|
| $\overline{\text{PB RESET}}$ | Push Button Reset Input. This debounced input will ignore pulses of less than 1 ms and is guaranteed to respond to pulses greater than 20 ms. |
| TD | Time Delay Set allows the user to select the maximum amount of time the ADM1232A will allow the $\overline{\text{STROBE}}$ input to remain inactive (i.e., $\overline{\text{STROBE}}$ is not receiving any high-to-low transitions), without forcing the ADM1232A to generate a RESET pulse. (See $\overline{\text{STROBE}}$ specifications, Figure 4 and the note on $\overline{\text{STROBE}}$ timeout selection.) |
| TOLERANCE | Tolerance Input. This input will determine how much the supply voltage will be allowed to decrease (as a percentage tolerance) before a RESET is asserted. Connect to V_{CC} for 10% and GND for 5%. |
| GND | 0 V ground reference for all signals. |
| RESET | Active high logic output. Will be asserted when: <ol style="list-style-type: none"> V_{CC} decreases below the amount specified by the TOLERANCE input or, $\overline{\text{PB RESET}}$ is forced low or, If there are no high-to-low transitions within the limits set by TD at $\overline{\text{STROBE}}$ or, During power-up. |
| $\overline{\text{RESET}}$ | Inverse of RESET, with an open drain output. |
| $\overline{\text{STROBE}}$ | The $\overline{\text{STROBE}}$ input is used to monitor the activity of a microprocessor. If there are no high-to-low transitions within the time specified by TD, a reset will be asserted. |
| V_{CC} | Power supply input +5 V. |

PIN CONFIGURATIONS



CIRCUIT INFORMATION

PB RESET

The $\overline{\text{PB RESET}}$ input makes it possible to manually reset a system using either a standard push-button switch or a logic low input. An internal debounce circuit provides glitch immunity when used with a switch, reducing the effects of glitches on the line. The debounce circuit is guaranteed to cause the ADM1232A to assert a reset if $\overline{\text{PB RESET}}$ is brought low for more than 20 ms and is guaranteed to ignore low inputs of less than 1 ms.

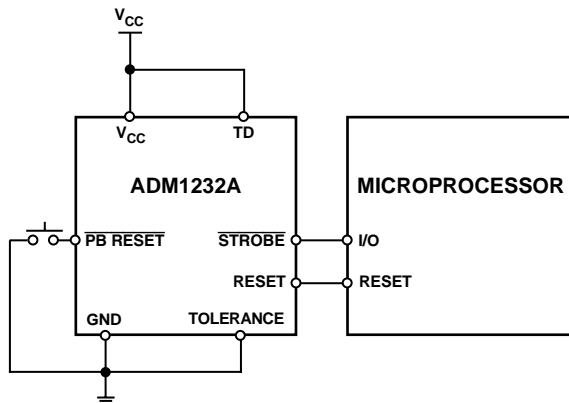


Figure 2. Typical Push Button Reset Application

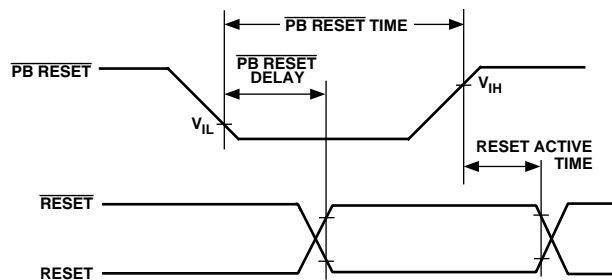


Figure 3. $\overline{\text{PB RESET}}$

STROBE Timeout Selection

TD or time delay set is used to set the Strobe Timeout Period. The Strobe Timeout Period is defined as being the maximum time between high-to-low transitions (Figure 4) that $\overline{\text{STROBE}}$ will accept before a reset will be asserted. The Strobe timeout settings are listed in Table I.

Table I.

| Condition | Min | Typ | Max | Units |
|----------------------|------|------|------|-------|
| TD = 0 V | 62.5 | 150 | 250 | ms |
| TD = Floating | 250 | 600 | 1000 | ms |
| TD = V _{CC} | 500 | 1200 | 2000 | ms |

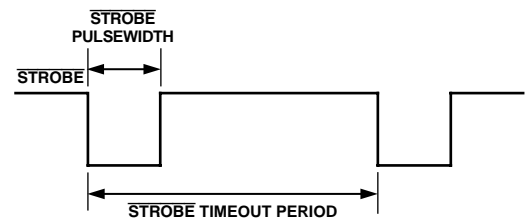


Figure 4. $\overline{\text{STROBE}}$ Parameters

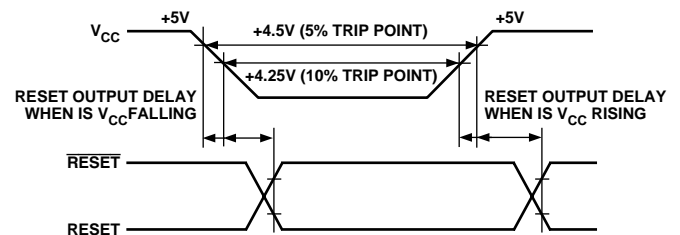


Figure 5. Reset Output Delay

TOLERANCE

The TOLERANCE input is used to determine the level V_{CC} can vary below 5 V without the ADM1232A asserting a reset. Connecting TOLERANCE to ground will select a -5% tolerance level and will cause the ADM1232A to generate a reset if V_{CC} falls below 4.75 V (typical). If TOLERANCE is connected to V_{CC} a -10% tolerance level is selected and will cause the ADM1232A to generate a reset if V_{CC} falls below 4.5 V (typical). Check the parameters for the V_{CC} trip point in the ADM1232A Specifications for more information.

RESET AND $\overline{\text{RESET}}$ OUTPUTS

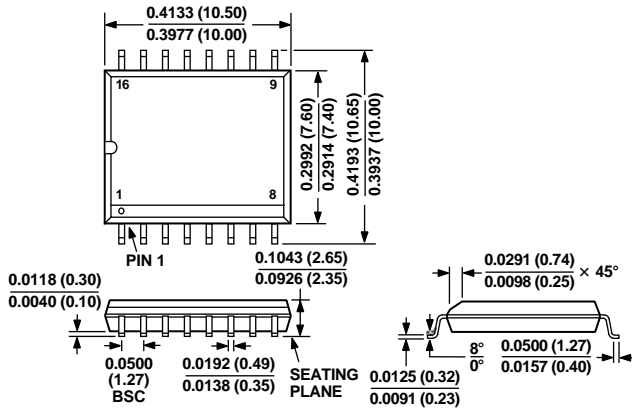
While RESET is capable of sourcing and sinking current, $\overline{\text{RESET}}$ is an open drain MOSFET which sinks current only. Therefore, it is necessary to pull this output high.

ADM1232A

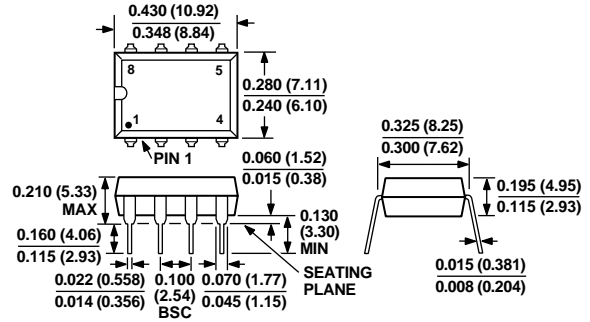
OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

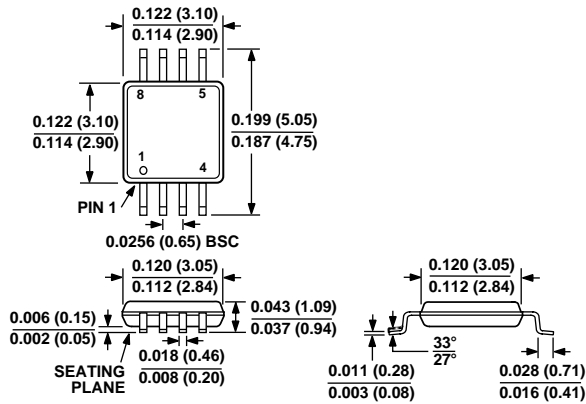
16-Lead Wide SOIC (R-16)



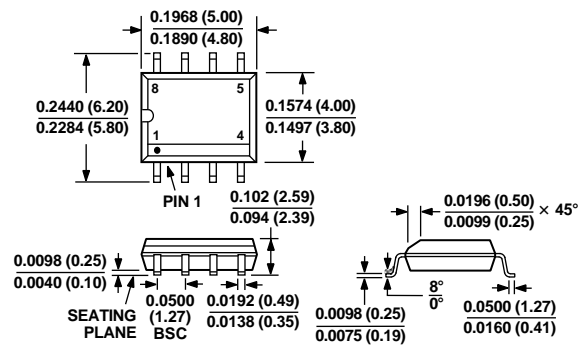
8-Lead PDIP (N-8)



8-Lead μ SOIC (RM-8)



8-Lead Narrow SOIC (R-8)



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